

## **isc** Silicon NPN Darlington Power Transistor

# 2SD2494

## DESCRIPTION

- Collector-Emitter Breakdown Voltage-
  - : V<sub>(BR)CEO</sub>= 110V(Min)
- High DC Current Gain-
- : h<sub>FE</sub>= 5000( Min.) @(I<sub>C</sub>= 5A, V<sub>CE</sub>= 4V)
- · Low Collector Saturation Voltage-
- : V<sub>CE(sat)</sub>= 2.5V(Max)@ (I<sub>C</sub>= 5A, I<sub>B</sub>= 5mA)
- Complement to Type 2SB1625
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

### **APPLICATIONS**

lc

 $I_B$ 

Pc

ΤJ

Tstg

 Designed for audio, series regulator and general purpose applications.

| SYMBOL           | PARAMETER                 | VALUE |
|------------------|---------------------------|-------|
| V <sub>CBO</sub> | Collector-Base Voltage    | 110   |
| V <sub>CEO</sub> | Collector-Emitter Voltage | 110   |
| V <sub>EBO</sub> | Emitter-Base Voltage      | 5     |

Collector Current-Continuous

**Base Current-Continuous** 

**Collector Power Dissipation** 

Junction Temperature

Storage Temperature

@Tc=25°C

UNIT

V

V

V

A

А

W

°C

°C

6

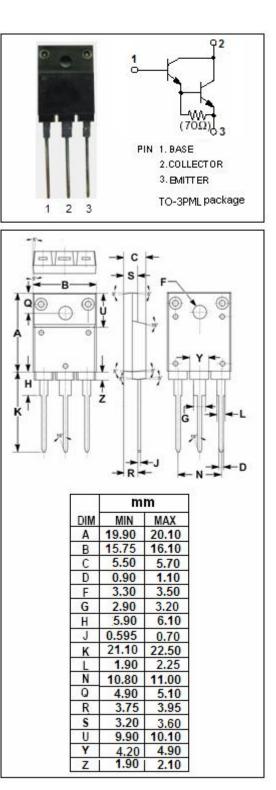
1

60

150

-55~150

## ABSOLUTE MAXIMUM RATINGS(Ta=25℃)



isc website: www.iscsemi.com



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## **ELECTRICAL CHARACTERISTICS**

#### Tj=25℃ unless otherwise specified

| SYMBOL                | PARAMETER                            | CONDITIONS                                                          | MIN  | TYP. | МАХ | UNIT |
|-----------------------|--------------------------------------|---------------------------------------------------------------------|------|------|-----|------|
| V <sub>(BR)CEO</sub>  | Collector-Emitter Breakdown Voltage  | I <sub>C</sub> = 30mA ; I <sub>B</sub> = 0                          | 110  |      |     | V    |
| V <sub>CE(sat)</sub>  | Collector-Emitter Saturation Voltage | I <sub>C</sub> = 5A; I <sub>B</sub> = 5mA                           |      |      | 2.5 | V    |
| V <sub>BE</sub> (sat) | Base-Emitter Saturation Voltage      | I <sub>C</sub> = 5A; I <sub>B</sub> = 5mA                           |      |      | 3.0 | V    |
| I <sub>CBO</sub>      | Collector Cutoff Current             | V <sub>CB</sub> = 110V; I <sub>E</sub> = 0                          |      |      | 100 | μA   |
| Іево                  | Emitter Cutoff Current               | V <sub>EB</sub> = 5V; I <sub>C</sub> = 0                            |      |      | 100 | μA   |
| h <sub>FE</sub>       | DC Current Gain                      | I <sub>C</sub> = 5A; V <sub>CE</sub> = 4V                           | 5000 |      |     |      |
| Сов                   | Output Capacitance                   | I <sub>E</sub> = 0; V <sub>CB</sub> = 10V; f <sub>test</sub> = 1MHz |      | 55   |     | pF   |
| f <sub>T</sub>        | Current-Gain—Bandwidth Product       | I <sub>E</sub> = -0.5A ; V <sub>CE</sub> = 12V                      |      | 60   |     | MHz  |

#### h<sub>FE</sub> Classifications

| 0          | Р          | Y           |
|------------|------------|-------------|
| 5000-12000 | 6500-20000 | 15000-30000 |

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